

MA3XD11

Silicon epitaxial planar type

For high-frequency rectification

■ Features

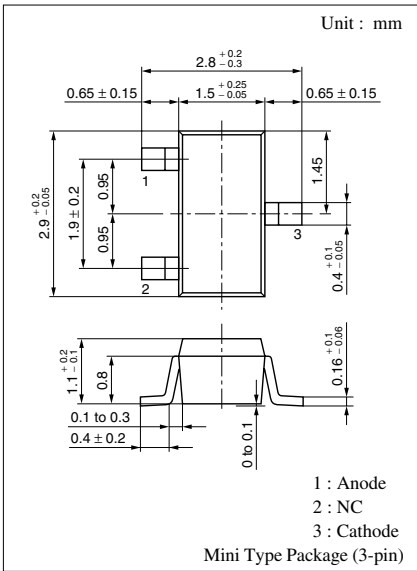
- Sealed in the Mini type 3-pin package
- Allowing to rectify under ($I_{F(AV)} = 1\text{ A}$) condition
- Low forward rise voltage V_F

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	20	V
Repetitive peak reverse voltage	V_{RRM}	25	V
Average forward current*1	$I_{F(AV)}$	1.0	A
Non-repetitive peak forward surge current*2	I_{FSM}	3	A
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

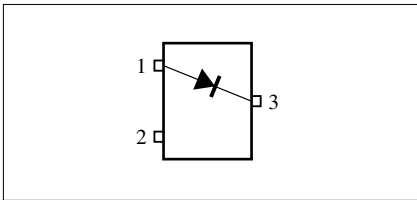
Note) *1 : With a alumina PC board

*2 : The peak-to-peak value in one cycle of 50 Hz sine-wave
(non-repetitive)



Marking Symbol: M6K

Internal Connection



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 20\text{ V}$			200	μA
Forward voltage (DC)	V_F	$I_F = 1.0\text{ A}$			0.45	V
Terminal capacitance	C_t	$V_R = 0\text{ V}, f = 1\text{ MHz}$		180		pF

- Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment
2. Rated input/output frequency: 400 MHz

